

ABSTRACT OF THE DISCLOSURE

A method for fabricating a semiconductor a
semiconductor device having a stacked-gate structure. A
polysilicon layer is formed overlying a substrate, which is
5 insulated from the substrate by a dielectric layer. A
metal-flash layer is formed overlying the polysilicon layer,
and then a tungsten nitride layer is formed overlying the
titanium layer. The tungsten nitride layer is annealed
using nitrogen and hydrogen gases. A tungsten layer and a
10 cap layer are successively formed overlying the tungsten
nitride layer.